

Session Title:	[MC1] High Aspect Feature Etching
Session Date:	November 14 (Mon.), 2022
Session Time:	13:00-14:30
Session Room:	Room C (Grand Ballroom 2, 2F)
Session Chair:	Prof. Heeyeop Chae (Sungkyunkwan Univ., Korea)

[MC1-1] [Invited] 13:00-13:30

Nanoscale Dry Processes for Controlling Atomic Layer Reactions and Fabrication of High-Aspect-Ratio Features

Kenji Ishikawa, T-T-Nga Nguye, Takayoshi Tsutsumi, S-N Hsaio, Makoto Sekine, and Masaru Hori (Nagoya Univ., Japan)

[MC1-2] [Invited] 13:30-14:00

The Use of Fluorinated Ethers for Plasma Etching of SiO₂

Sanghyun You and Chang-Koo Kim (Ajou Univ., Korea)

[MC1-3] [Invited] 14:00-14:30

Independent Effect of Each Plasma Parameter on High Aspect Ratio (HAR) Oxide Etching Process at Low Frequency Bias Power Using ICP System

Hye Jun Son, Gilyoung Choi, and Kwang-Ho Kwon (Korea Univ., Korea)